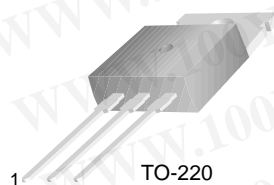


## BDX34/A/B/C

BDX34/A/B/C

### Power Linear and Switching Applications

- High Gain General Purpose
- Power Darlington TR
- Complement to BDX33/33A/33B/33C respectively



TO-220  
1.Base 2.Collector 3.Emitter

### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage		
	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
$V_{CEO}$	Collector-Emitter Voltage		
	: BDX34	- 45	V
	: BDX34A	- 60	V
	: BDX34B	- 80	V
	: BDX34C	- 100	V
$I_C$	Collector Current (DC)	- 10	A
$I_{CP}$	*Collector Current (Pulse)	- 15	A
$I_B$	Base Current	- 0.25	A
$P_C$	Collector Dissipation ( $T_C=25^\circ\text{C}$ )	70	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

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**Electrical Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$V_{CE0}(\text{sus})$	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	$I_C = -100\text{mA}, I_B = 0$	- 45 - 60 - 80 - 100			V V V V
$V_{CER}(\text{sus})$	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	$I_C = -100\text{mA}, I_B = 0$ $R_{BE} = 100\Omega$	- 45 - 60 - 80 - 100			V V V V
$V_{CEV}(\text{sus})$	* Collector-Emitter Sustaining Voltage : BDX34 : BDX34A : BDX34B : BDX34C	$I_C = -100\text{mA}, I_B = 0$ $V_{BE} = -1.5\text{V}$	- 45 - 60 - 80 - 100			V V V V
$I_{CBO}$	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	$V_{CB} = -45\text{V}, I_E = 0$ $V_{CB} = -60\text{V}, I_E = 0$ $V_{CB} = -80\text{V}, I_E = 0$ $V_{CB} = -100\text{V}, I_E = 0$			- 0.2 - 0.2 - 0.2 - 0.2	mA mA mA mA
$I_{CEO}$	Collector Cut-off Current : BDX34 : BDX34A : BDX34B : BDX34C	$V_{CE} = -22\text{V}, I_B = 0$ $V_{CE} = -30\text{V}, I_B = 0$ $V_{CE} = -40\text{V}, I_B = 0$ $V_{CE} = -50\text{V}, I_B = 0$			- 0.5 - 0.5 - 0.5 - 0.5	mA mA mA mA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -5\text{V}, I_C = 0$			- 5	mA
$h_{FE}$	* DC Current Gain : BDX34/34A : BDX34B/34C	$V_{CE} = -3\text{V}, I_C = -4\text{A}$ $V_{CE} = -3\text{V}, I_C = -3\text{A}$	750 750			
$V_{CE}(\text{sat})$	* Collector-Emitter Saturation Voltage : BDX34/34A : BDX34B/34C	$I_C = -4\text{A}, I_B = -8\text{mA}$ $I_C = -3\text{A}, I_B = -6\text{mA}$			- 2.5 - 2.5	V V
$V_{BE}(\text{on})$	* Base-Emitter ON Voltage : BDX34/34A : BDX34B/34C	$V_{CE} = -3\text{V}, I_C = -4\text{A}$ $V_{CE} = -3\text{V}, I_C = -3\text{A}$			- 2.5 - 2.5	V V
$V_F$	* Parallel Diode Forward Voltage	$I_F = -8\text{A}$			- 4	V

\* Pulse Test: PW=300 $\mu\text{s}$ , duty Cycle =1.5% Pulsed

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BDX34/A/B/C

## Typical Characteristics

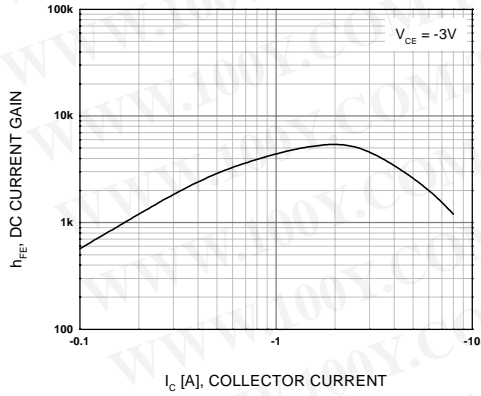


Figure 1. DC Current Gain

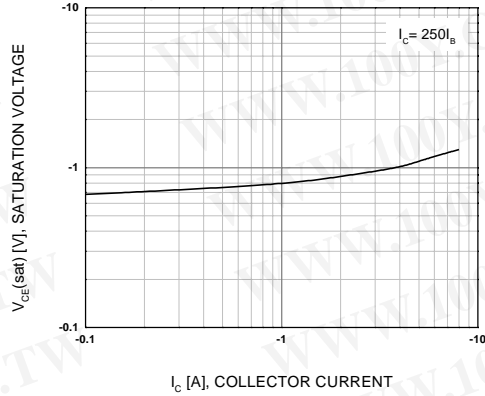


Figure 2. Collector-Emitter Saturation Voltage

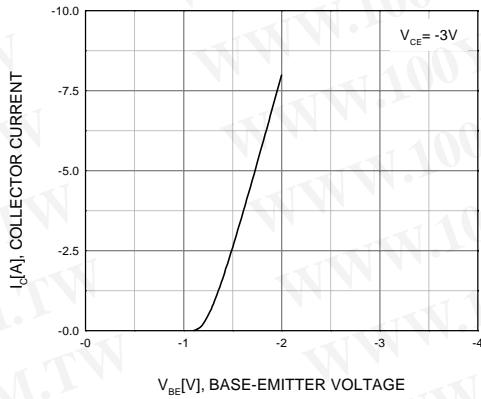


Figure 3. Base-Emitter On Voltage

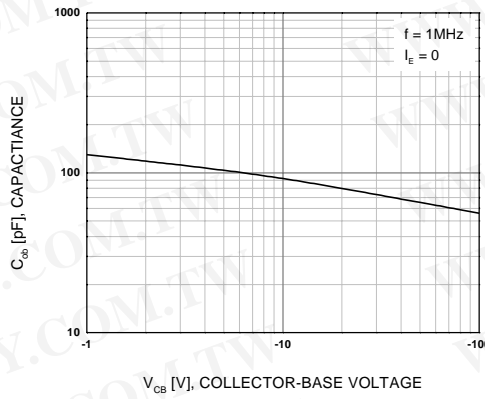


Figure 4. Output Capacitance

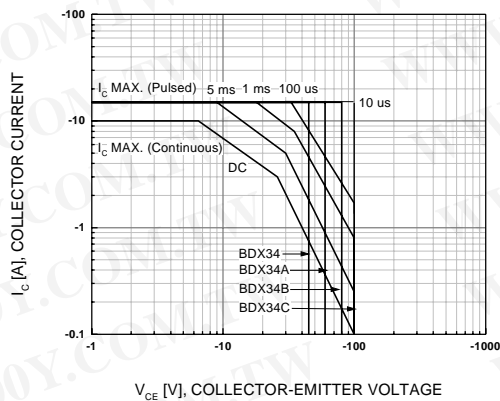


Figure 5. Safe Operating Area

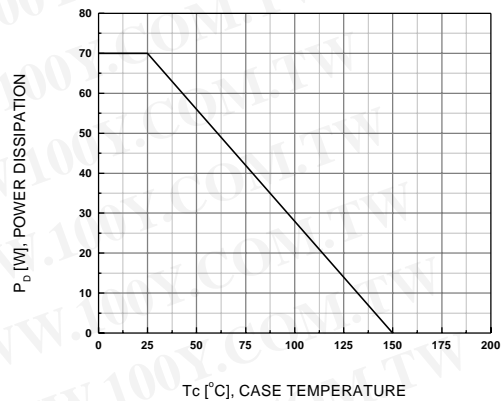


Figure 6. Power Derating



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